



# The EU Framework Programme for Research and Innovation



**A generic CMOS-compatible platform for co-integrated plasmonic/photonic/electronic PICs towards volume manufacturing of low energy, small size and high performance photonic devices**



plasmofab.eu

## Factsheet

### Coordinator

Aristotle University of Thessaloniki

### Funding

This project has received funding from the European Union's Horizon 2020 research and innovation programme EU-H2020-RIA-ICT-27 under Grand Agreement No: 688166

### Total Budget/EC Contribution

€ 4,150,246.25 / € 3,580,691.135

### Project Launch : January 2016

Duration : 36 months

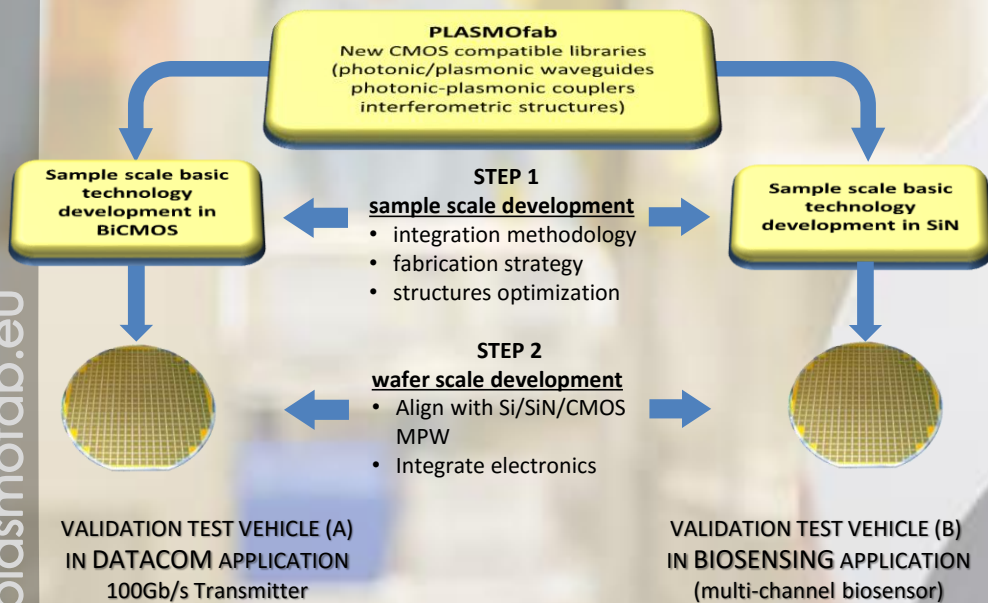
## Consortium

- Aristotle University of Thessaloniki (Coordinator) (GR)
- Universite de Bourgogne (F)
- Swiss Federal Institute of Technology in Zurich (CH)
- AMO GmbH (DE)
- ams AG (A)
- Micram GmbH (DE)
- Saarland University (DE)
- Mellanox Technologies (IL)
- Phoenix BV (N)
- AIT Austrian Institute of Technology GmbH (A)

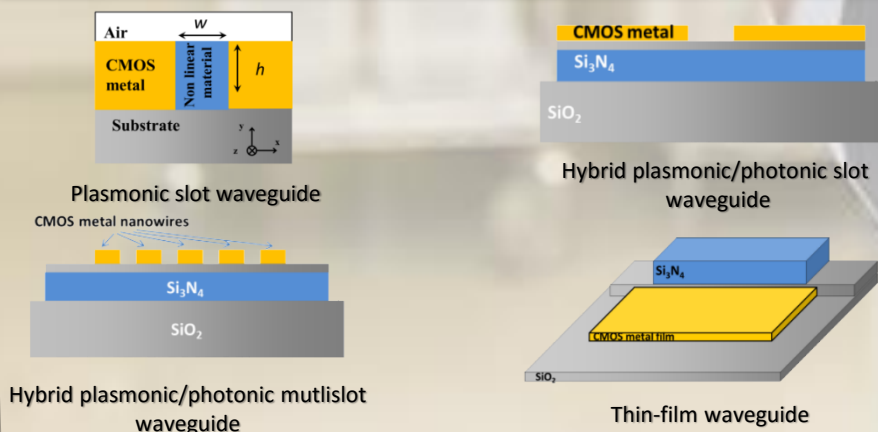
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# What is PLASMOFAB?

**PLASMOFAB** aims to develop CMOS compatible plasmonics in a generic planar integration process as the means to consolidate photonic and electronic integration. Wafer scale integration will be used by PLASMOfab to demonstrate low cost, volume manufacturing and high yield of powerful PICs. The new integration technology will unravel a series of innovations with profound benefits of enhanced high light-matter interaction enabled by plasmonics in optical transmitters and biosensors modules.



## Plasmonic waveguides investigated in PLASMOFAB



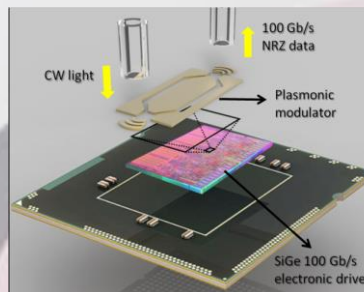
# PLASMOFAB Overview

## What are the Innovation challenges?

- Full characterization of CMOS metals (Al, TiN, Cu) on Si, SiO<sub>2</sub> and SiN platforms
- Co-integration of CMOS-compatible metals with photonics
- New CMOS-compatible planar plasmonic structures
- Fully comply to CMOS fab processes (deposition temp, thickness, dimensions etc)
- Blend plasmonics, photonics and microfluidics in the same platform

## PLASMOFAB Demonstration Modules

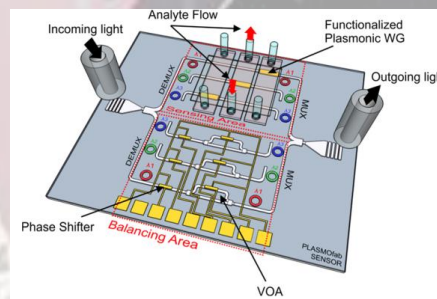
### A low-power and low-insertion loss plasmonic modulator



BiCMOS processes to develop and co-integrate the driver and the plasmonic modulator on a single chip

- ✓ Monolithic integration of opto-electro-plasmonic modulator
- ✓ 100 Gb/s SiGe electronic driver
- ✓ Optimized for differential NRZ modulation exceeding 100Gb/s (e.g. 112Gb/s)

### An ultra-sensitive multichannel plasmonic sensor for lab-on-chip applications



Demonstrate concurrent detection of multiple inflammation biomarkers for early diagnosis and prognosis

- ✓ Ultra-sensitive multi-channel Si<sub>3</sub>N<sub>4</sub>-based molecular plasmonic-photonic biosensor on-chip
- ✓ Combination of sensing with high-speed surface functionalization techniques and microfluidics